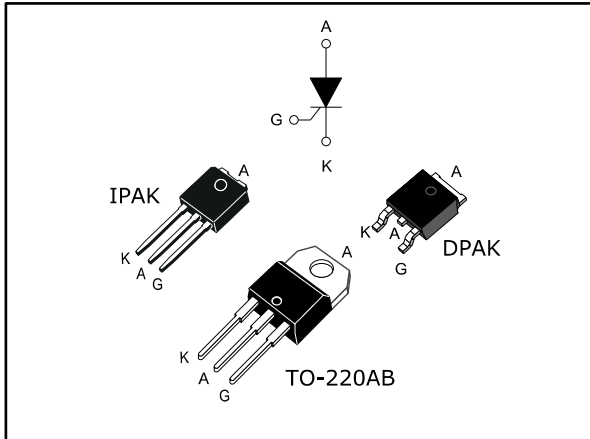


Sensitive gate 4 A SCRs

Datasheet - production data



**Description**

Thanks to highly sensitive triggering levels, the device is suitable for all applications where the available gate current is limited, such as motor control for hand tools, kitchen aids, overvoltage crowbar protection for low power supplies among others.

Available in through-hole and surface-mount packages, they provide an optimized performance in a limited space area.

Table 1: Device summary

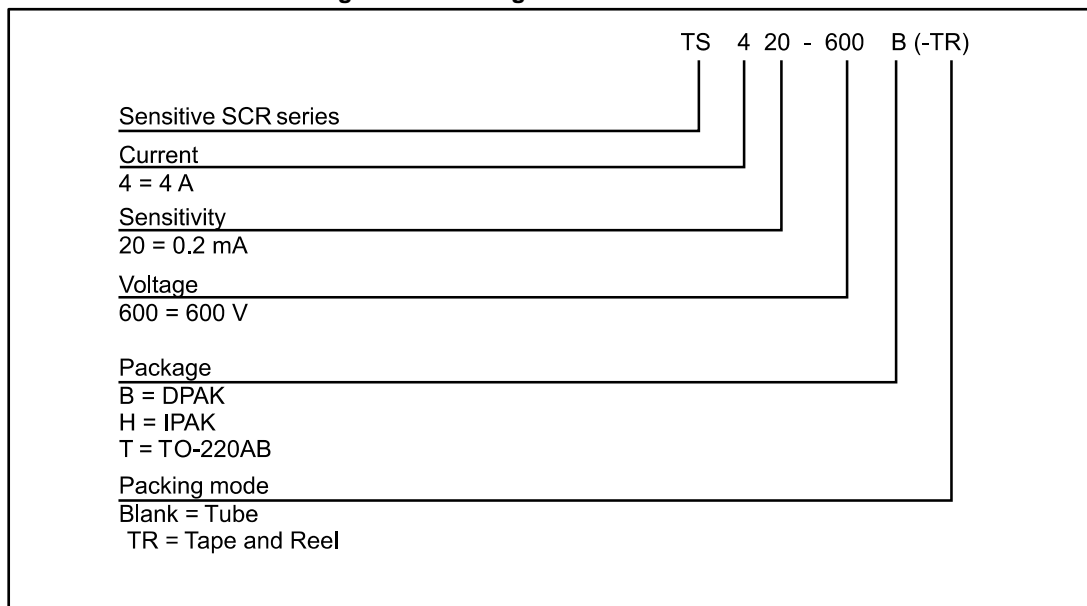
Order code	Sensitivity	Package
TS420-600B	0.2 mA	DPAK
TS420-600H		IPAK
TS420-600T		TO-220AB

**Features**

- On-state RMS current: 4 A
- Repetitive peak off-state voltage ( $V_{DRM}$ ,  $V_{RRM}$ ) 600 V
- Triggering gate current,  $I_{GT}$  0.2 mA

**1 Ordering information**

Figure 1: Ordering information scheme



## 2 Characteristics

**Table 2: Absolute ratings (limiting values)**

Symbol	Parameter		Value	Unit	
$I_{T(RMS)}$	RMS on-state current (180 ° conduction angle)		$T_C = 115^\circ\text{C}$	4	A
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)		$T_C = 115^\circ\text{C}$	2.5	A
$I_{TSM}$	Non repetitive surge peak on-state current	$t_p = 8.3\text{ ms}$	$T_{j\text{ initial}} = 25^\circ\text{C}$	33	A
		$t_p = 10\text{ ms}$		30	
$I^2t$	$I^2t$ value for fusing	$t_p = 10\text{ ms}$	$T_j = 25^\circ\text{C}$	4.5	A <sup>2</sup> s
$di/dt$	Critical rate of rise of on-state current $I_G = 10\text{ mA}$ , $di_G/dt = 0.1\text{ A}/\mu\text{s}$	$f = 60\text{ Hz}$	$T_j = 125^\circ\text{C}$	50	A/ $\mu\text{s}$
$I_{GM}$	Peak gate current	$t_p = 20\text{ }\mu\text{s}$		1.2	A
$P_{G(AV)}$	Average gate power dissipation			0.2	W
$V_{RGM}$	Maximum peak reverse gate voltage			5	V
$T_{stg}$	Storage junction temperature range			-40 to +150	°C
$T_j$	Maximum operating junction temperature			-40 to +125	°C

**Table 3: Device timings**

Symbol	Parameter	Test conditions	Value	Unit
$t_{GT}$	Gate controlled turn on time	$I_{TM} = 10\text{ A}$ , $T_j = 25^\circ\text{C}$ , $V_D = V_{DRM(max.)}$ , $I_{GT} = 10\text{ mA}$ , $di_G/dt = 0.2\text{ A}/\mu\text{s}$ , $R_G = 1\text{ k}\Omega$	0.5 (typ.)	$\mu\text{s}$
$t_Q$	Circuit controlled turn off time	$I_{TM} = 8\text{ A}$ , $T_j = 125^\circ\text{C}$ , $V_D = 67\% V_{DRM(max.)}$ , $V_R = 10\text{ V}$ , $dI_T/dt = 10\text{ A}/\mu\text{s}$ , $dV_D/dt = 2\text{ V}/\mu\text{s}$ , $R_G = 1\text{ k}\Omega$	60 (typ.)	

**Table 4: Electrical characteristics ( $T_j = 25\text{ °C}$  unless otherwise specified)**

Symbol	Test Conditions		Value	Unit		
$I_{GT}$	$V_D = 12\text{ V}, R_L = 33\ \Omega$		Max.	200	$\mu\text{A}$	
$V_{GT}$			Max.	0.8	V	
$V_{GD}$	$V_D = V_{DRM}, R_L = 33\text{ k}\Omega, R_{GK} = 220\ \Omega$	$T_j = 125\text{ °C}$	Min.	0.1	V	
$I_H$	$I_T = 50\text{ mA}, R_{GK} = 1\text{ k}\Omega$		Max.	5	mA	
$I_L$	$I_G = 2\text{ mA}, R_{GK} = 1\text{ k}\Omega$		Max.	6	mA	
$dV/dt$	$V_D = 67\% V_{DRM}, R_{GK} = 220\ \Omega$	$T_j = 125\text{ °C}$	Min.	5	$\text{V}/\mu\text{s}$	
$V_{TM}$	$I_{TM} = 8\text{ A}, t_P = 380\ \mu\text{s}$		$T_j = 25\text{ °C}$	Max.	1.6	V
$V_{T0}$	Threshold voltage		$T_j = 125\text{ °C}$	Max.	0.85	V
$R_D$	Dynamic resistance		$T_j = 125\text{ °C}$	Max.	90	$\text{m}\Omega$
$I_{DRM}$	$V_D = V_R = V_{DRM} = V_{RRM}, R_{GK} = 220\ \Omega$		$T_j = 25\text{ °C}$	Max.	5	$\mu\text{A}$
$I_{RRM}$			$T_j = 125\text{ °C}$		1	mA

**Table 5: Thermal parameters**

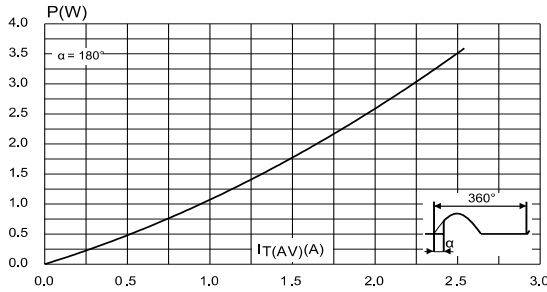
Symbol	Parameter		Value	Unit	
$R_{th(j-c)}$	Junction to case (DC)		3.0	$\text{°C}/\text{W}$	
$R_{th(j-a)}$	Junction to ambient (DC)	$S^{(1)} = 0.5\text{ cm}^2$	70		
			IPAK		100
			TO-220AB		60

**Notes:**

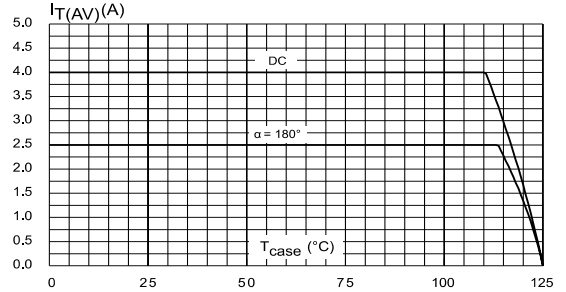
(1)Copper surface under tab

**2.1 Characteristics (curves)**

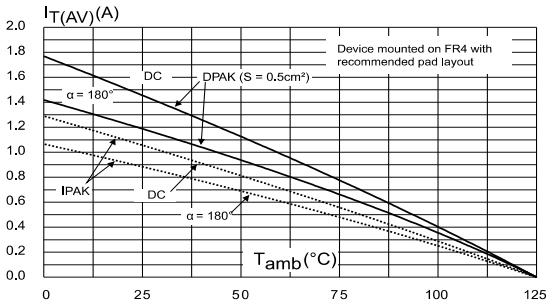
**Figure 2: Maximum average power dissipation versus average on-state current**



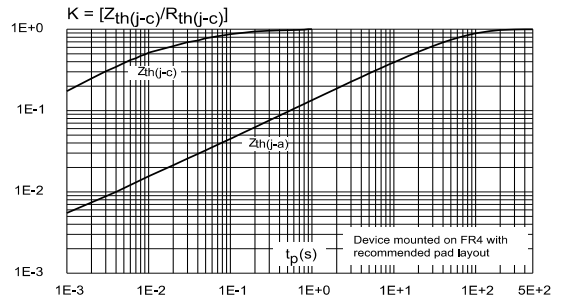
**Figure 3: Average and DC on-state current versus case temperature**



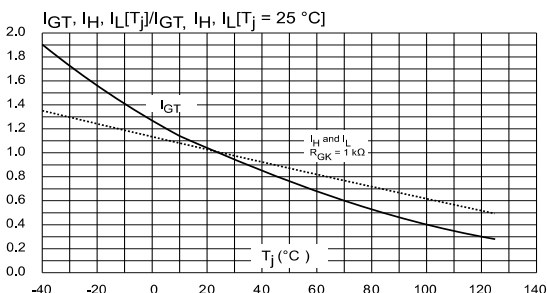
**Figure 4: Average and D.C. on state current versus ambient temperature (DPAK)**



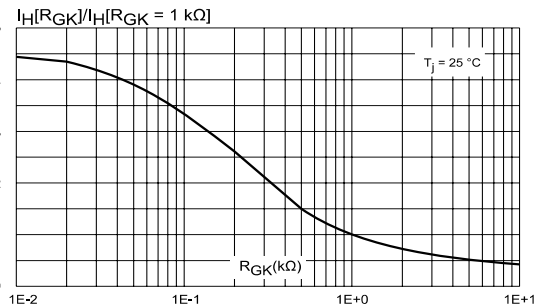
**Figure 5: Relative variation of thermal impedance junction to ambient versus pulse duration (DPAK)**



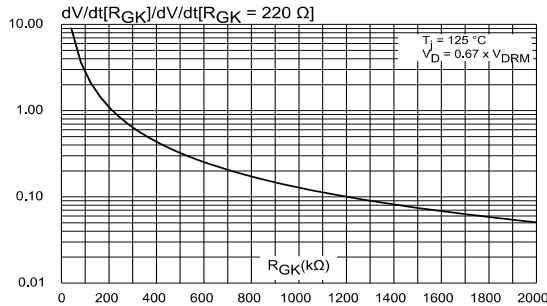
**Figure 6: Relative variation of gate trigger current and holding current versus junction temperature**



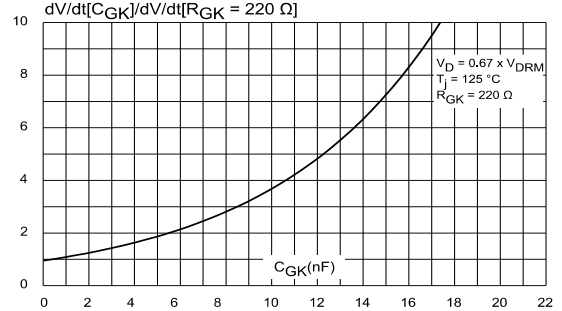
**Figure 7: Relative variation of holding current versus gate-cathode resistance (typical values)**



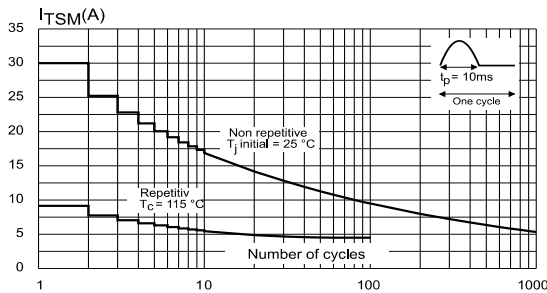
**Figure 8: Relative variation of dV/dt immunity versus gate-cathode resistance (typical values)**



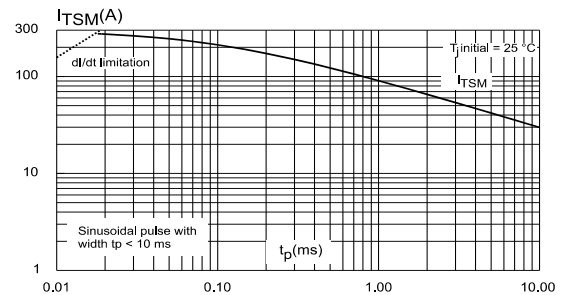
**Figure 9: Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values)**



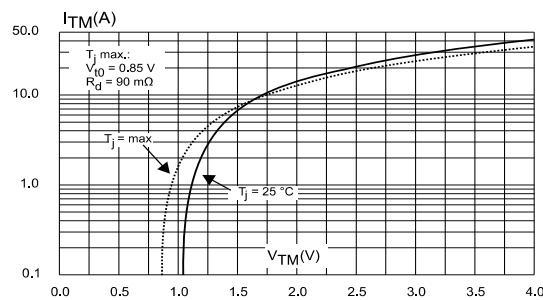
**Figure 10: Surge peak on-state current versus number of cycles**



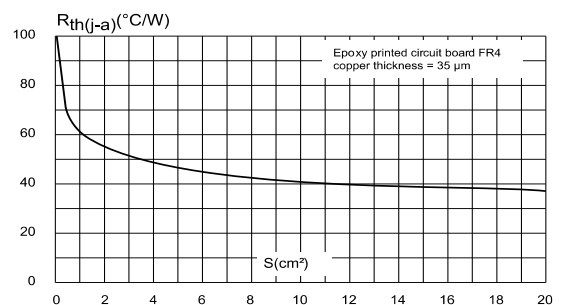
**Figure 11: Non-repetitive surge peak on-state current**



**Figure 12: On-state characteristics (maximum values)**



**Figure 13: Thermal resistance junction to ambient versus copper surface under tab**



### 3 Package information

- Lead-free packages
- Recommended torque value: 0.4 to 0.6 N·m

#### 3.1 DPAK package information

Figure 14: DPAK package outline

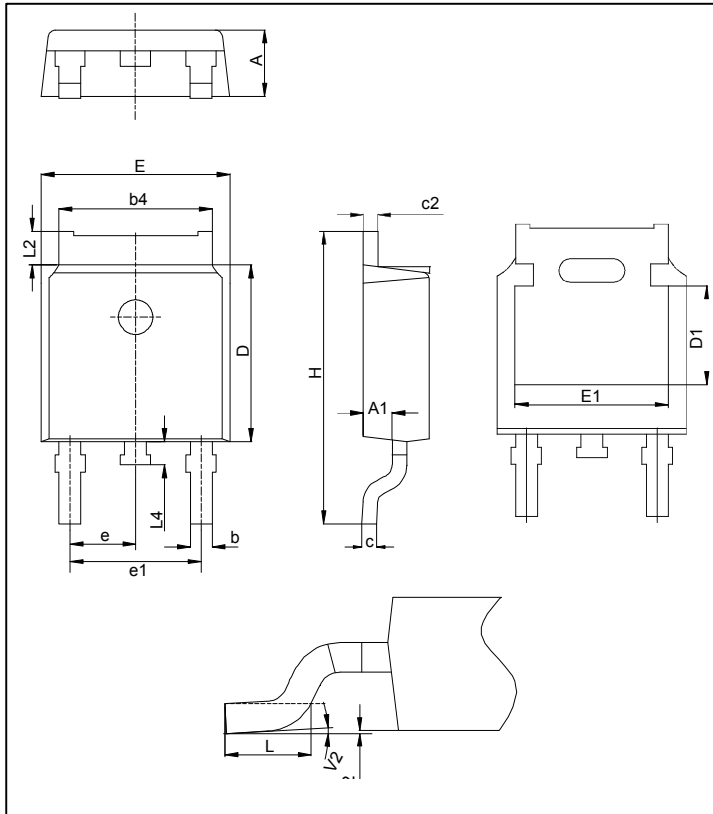


Table 6: DPAK package mechanical data

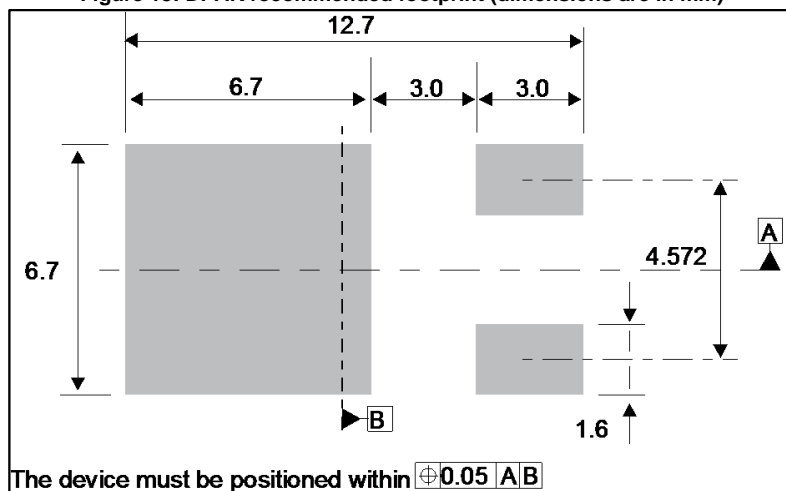
Ref.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.18		2.40	0.0858		0.0945
A1	0.90		1.10	0.0354		0.0433
A2	0.03		0.23	0.0012		0.0091
b	0.64		0.90	0.0252		0.354
b4	4.95		5.46	0.1949		0.2150
c	0.46		0.61	0.0181		0.0240
c2	0.46		0.60	0.0181		0.0236
D	5.97		6.22	0.2350		0.2449
D1	5.10			0.2007		
E	6.35		6.73	0.2500		0.2650
E1	4.32			0.1701		
e		2.29			0.0900	
e1		4.57			0.1800	
H	9.35		10.40	0.3681		0.4094
L	1.00		1.78	0.0394		0.0701
L2			1.27			0.0500
L4	0.60		1.02	0.0236		0.0402
V2	0°		+8°	0°		+8°

**Notes:**

<sup>(1)</sup>Dimensions in inches are given for reference only

This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Figure 15: DPAK recommended footprint (dimensions are in mm)



**3.2 IPAK package information**

Figure 16: IPAK package outline

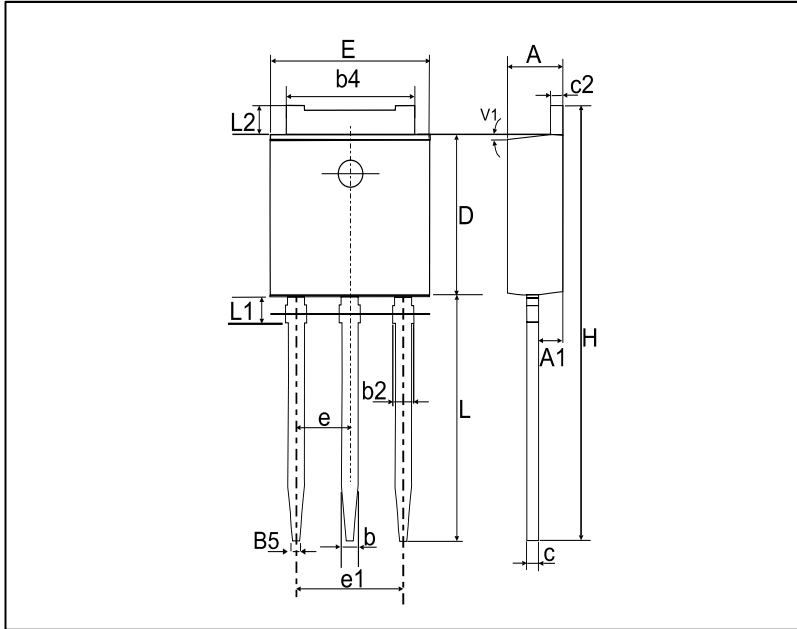



Table 7: IPAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.0866		0.0945
A1	0.90		1.10	0.0354		0.0433
b	0.64		0.90	0.0252		0.0354
b2			0.95			0.0374
b4	5.20		5.43	0.2047		0.2138
B5		0.30			0.0118	
c	0.45		0.60	0.0177		0.0236
c2	0.46		0.60	0.0181		0.0236
D	6.00		6.20	0.2362		0.2441
E	6.40		6.65	0.2520		0.2618
e		2.28			0.0898	
e1	4.40		4.60	0.1732		0.1811
H		16.10			0.6339	
L	9.00		9.60	0.3545		0.3780
L1	0.80		1.20	0.0315		0.0472
L2		0.80	1.25		0.0315	0.0492
V1		10°			10°	

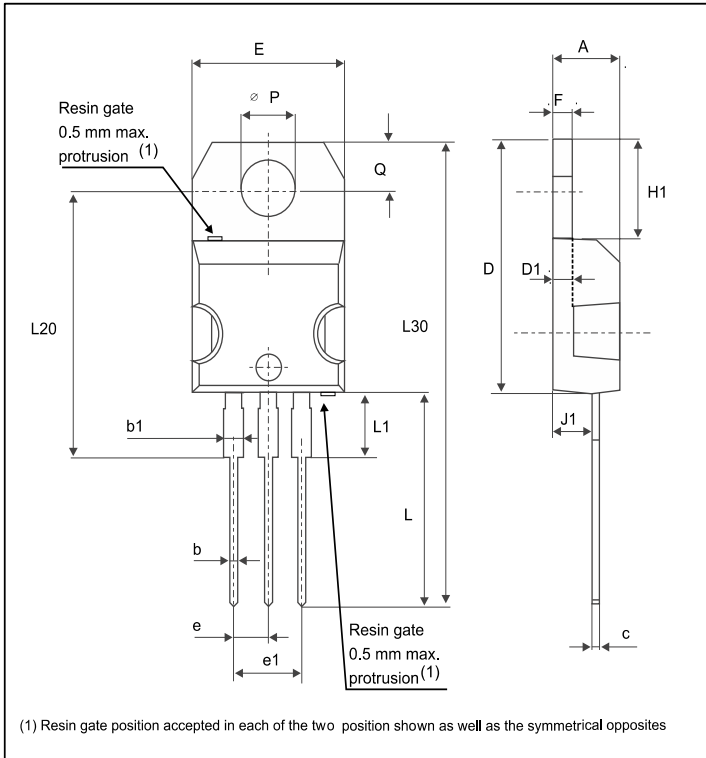
**Notes:**

<sup>(1)</sup>Inch dimensions are for reference only.

 This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

**3.3 TO-220AB package information**

**Figure 17: TO-220AB package outline**



**Table 8: TO-220AB package mechanical data**

Ref.	Dimensions			
	Millimeters		Inches <sup>(1)</sup>	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.1732	0.1811
b	0.61	0.88	0.0240	0.0346
b1	1.14	1.55	0.0449	0.0610
c	0.48	0.70	0.0189	0.0276
D	15.25	15.75	0.6004	0.6201
D1	1.27 typ.		0.0500 typ.	
E	10.00	10.40	0.3937	0.4094
e	2.40	2.70	0.0945	0.1063
e1	4.95	5.15	0.1949	0.2028
F	1.23	1.32	0.0484	0.0520
H1	6.20	6.60	0.2441	0.2598
J1	2.40	2.72	0.0945	0.1071
L	13.00	14.00	0.5118	0.5512
L1	3.50	3.93	0.1378	0.1547
L20	16.40 typ.		0.6457 typ.	
L30	28.90 typ.		1.1378 typ.	
ØP	3.75	3.85	0.1476	0.1516
Q	2.65	2.95	0.1043	0.1161

**Notes:**

<sup>(1)</sup>Inch dimensions are for reference only.

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